

Abstract Submitted  
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**Electric field tuning of magnetic properties in FeGa films on ferroelastic Pb(Zr,Ti)O<sub>3</sub> thin films probed by ferromagnetic resonance<sup>1</sup>**  
ARUN LUYKX, SAMUEL LOFLAND, VARATHARAJAN ANBUSATHAIAH, VALANOOR NAGARAJAN, FRANSISKA KARTAWIDJAJA, JOHN WANG, ICHIRO TAKEUCHI — In order to investigate the possibility of fabricating electric field tunable thin film magnetic devices using a multiferroic transduction effect, we have patterned Fe<sub>0.7</sub>Ga<sub>0.3</sub> (FeGa) films sputter-deposited on PbZr<sub>0.3</sub>Ti<sub>0.7</sub>O<sub>3</sub> (PZT(30/70))/PbZr<sub>0.7</sub>Ti<sub>0.3</sub>O<sub>3</sub> (PZT(70/30)) tetragonal/rhombohedral bilayers on Pt/Ti/SiO<sub>2</sub>/Si wafers. Previous piezoforce microscopy studies have shown that the PZT bilayers exhibit presence of ferroelastic domains where the fraction of the local *c/a* domain ratio can be tuned by an applied electric field. The FeGa top layer was patterned into 20 μm x 20 μm capacitor devices in order to apply electric field to the multilayers, and ferromagnetic resonance (FMR) measurements at 9.2 GHz were performed. Typically, a relatively sharp FMR signal observed before application of the electric field would get substantially broadened after initial application of +4 kV/cm. Angular dependent FMR indicates that magnetic anisotropy in the FeGa is indeed affected by application of electric field.

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